BYV410X-600

Enhanced ultrafast dual rectifier diode

Rev. 01 — 29 June 2009

Product data sheet

1. Product profile

1.1 General description

Enhanced ultrafast dual rectifier diode in a SOT186A (TO-220AB) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Isolated package
- Low thermal resistance

- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state losses

1.3 Applications

■ Dual mode (DCM and CCM) PFC

 Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5; $T_h \le 42$ °C; both diodes conducting; see Figure 1; see Figure 2	-	-	20	Α
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	20	35	ns
Q_r	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V};$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	15	28	nC
Static ch	aracteristics					
V _F	forward voltage	$I_F = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 4	-	1.4	2.1	V
		$I_F = 10 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	1.3	1.9	V



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1
3	A2	anode 2		<u> </u>
3 mb	n.c.	mounting base; isolated		sym125
			SOT186A (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	number Package					
	Name	Description	Version			
BYV410X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5; $T_h \le 42$ °C; both diodes conducting; see Figure 1; see Figure 2	-	20	Α
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5; t_p = 25 $\mu s;$ T_h ≤ 60 °C; per diode	-	20	Α
I _{FSM}	non-repetitive peak	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	132	Α
	forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ 25 °C; per diode	-	120	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

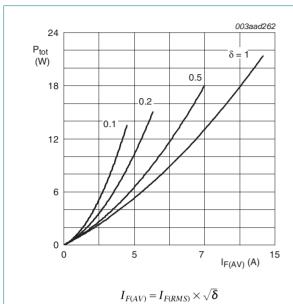


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

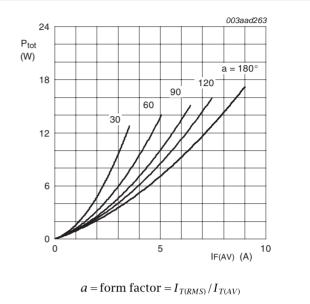


Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; per diode; see Figure 3	-	-	5	K/W
		with heatsink compound; both diodes conducting	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	55	-	K/W

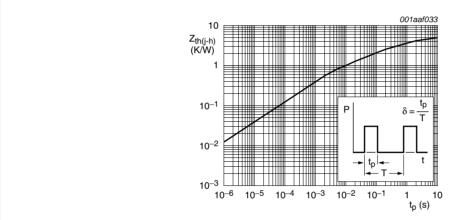


Fig 3. Transient thermal impedance from junction to heatsink per diode as a function of pulse width

6. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	$I_F = 10 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 4	-	1.4	2.1	V
		I _F = 10 A; T _j = 150 °C	-	1.3	1.9	V
I _R	reverse current	$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.7	1.5	mA
		$V_R = 600 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	50	μA
Dynamic o	characteristics					
Qr	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	15	28	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	20	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 5	-	1.4	1.9	Α
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 6	-	3.2	-	V

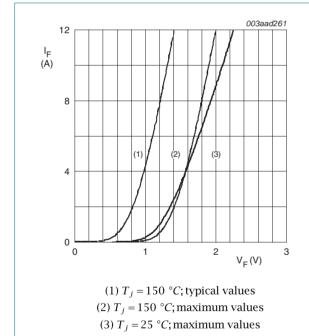


Fig 4. Forward current as a function of forward voltage

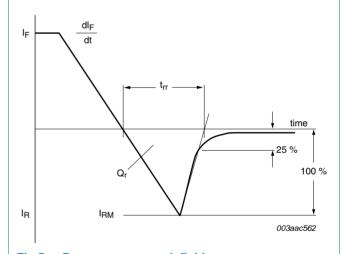
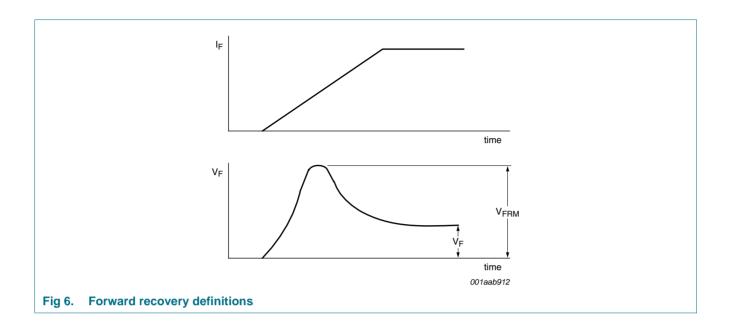


Fig 5. Reverse recovery definitions; ramp recovery

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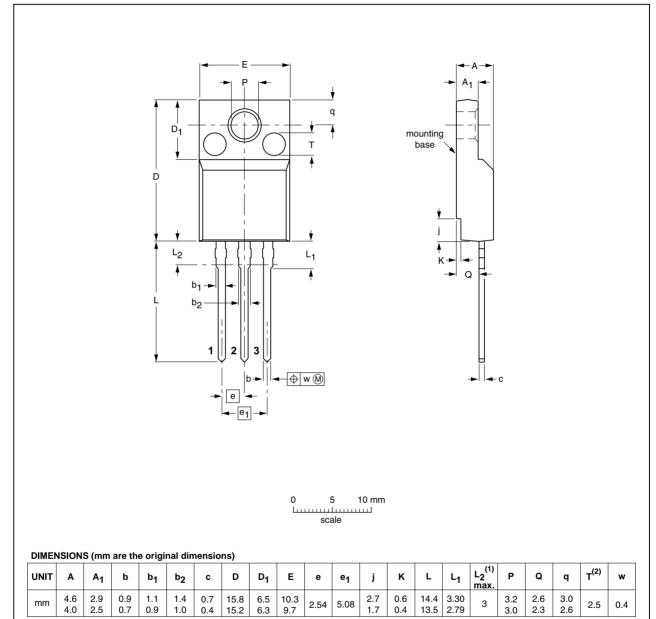


8. Package outline

Plastic single-ended package; isolated heatsink mounted;

1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



Notes

- 1. Terminal dimensions within this zone are uncontrolled
- 2. Both recesses are \varnothing 2.5 \times 0.8 max. depth

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT186A		3-lead TO-220F			02-04-09 06-02-14

Fig 7. Package outline SOT186A (TO-220F)



9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV410X-600_1	20090629	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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